Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-200	mA
Peak Pulse Collector Current	I_{CM}	-500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

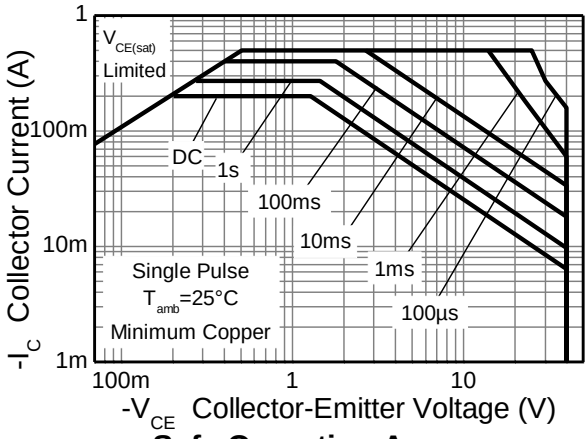
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	270	mW
	(Note 6)		925	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	465	°C/W
	(Note 6)		135	
Thermal Resistance, Junction to Lead	(Note 7)	$R_{\theta JL}$	135	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 8)

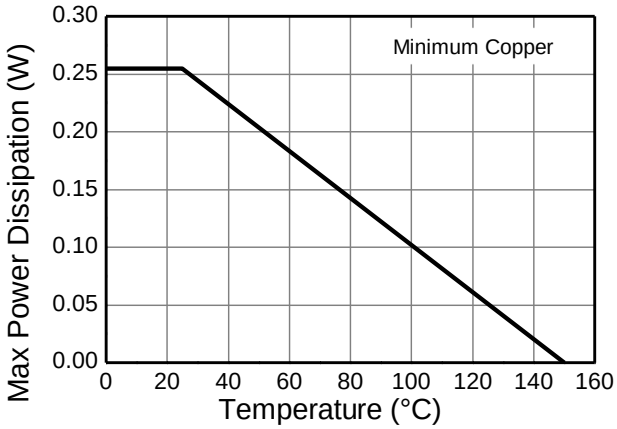
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

Notes:
5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
7. Thermal resistance from junction to solder-point (on the exposed collector pad).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

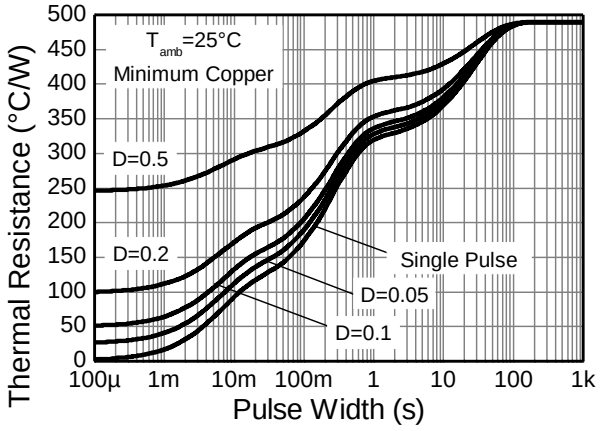
Thermal Characteristics and Derating Information



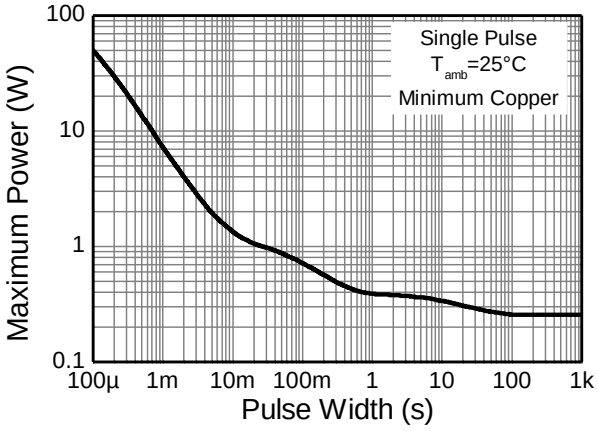
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	V	I_C = -100µA, I_E = 0
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	-40	—	V	I_C = -10.0mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	-6.0	—	V	I_E = -100µA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -3.0V
Collector Cutoff Current	I_{CBO}	—	-50	nA	V_{CB} = -30V, I_E = 0
Base Cutoff Current	I_{BL}	—	-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -3.0V
ON CHARACTERISTICS (Note 9)					
DC Current Gain	h_{FE}	60 80 100 60 30	— — 300 — —	—	I_C = -100µA, V_{CE} = -1.0V I_C = -1.0mA, V_{CE} = -1.0V I_C = -10mA, V_{CE} = -1.0V I_C = -50mA, V_{CE} = -1.0V I_C = -100mA, V_{CE} = -1.0V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	-0.25 -0.40	V	I_C = -10mA, I_B = -1.0mA I_C = -50mA, I_B = -5.0mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.65 —	-0.85 -0.95	V	I_C = -10mA, I_B = -1.0mA I_C =- 50mA, I_B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.5	pF	V_{CB} = -5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}	—	10	pF	V_{EB} = -0.5V, f = 1.0MHz, I_C = 0
Current Gain-Bandwidth Product	f_T	300	—	MHz	V_{CE} = -20V, I_C = -10mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	V_{CC} = -3.0V, I_C = -10mA, $V_{BE(off)}$ = 0.5V, I_{B1} = -1.0mA
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	225	ns	V_{CC} = -3.0V, I_C = -10mA, I_{B1} = I_{B2} = -1.0mA
Fall Time	t_f	—	75	ns	

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

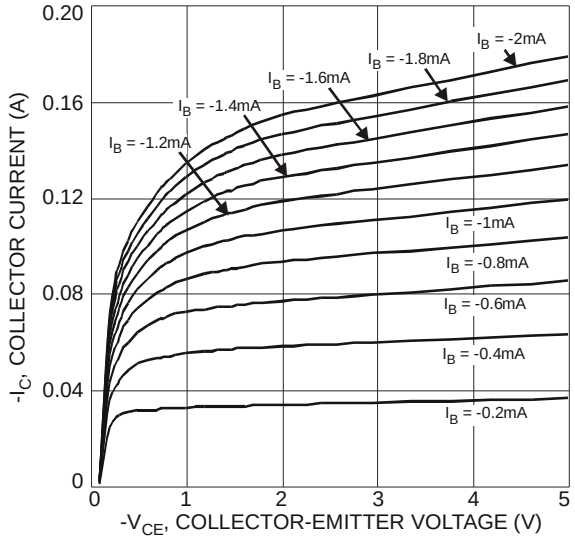


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

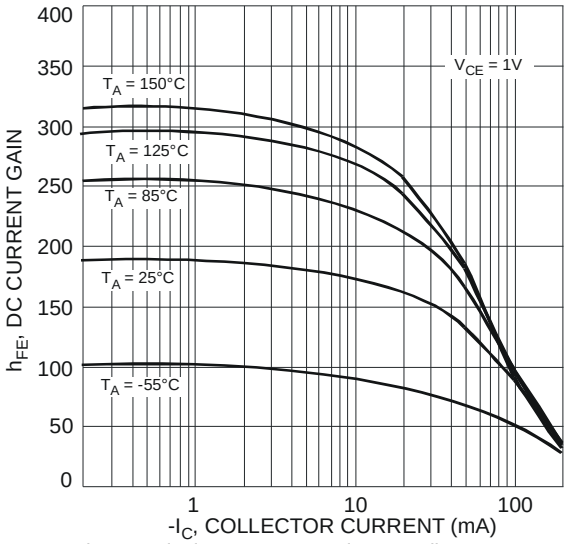


Fig. 5 Typical DC Current Gain vs. Collector Current

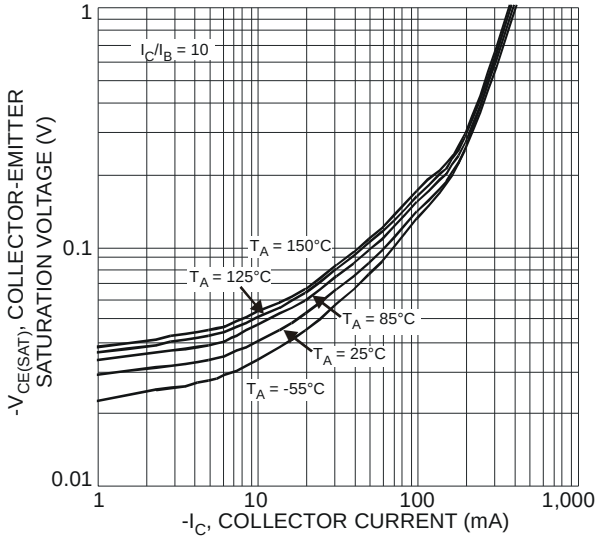


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

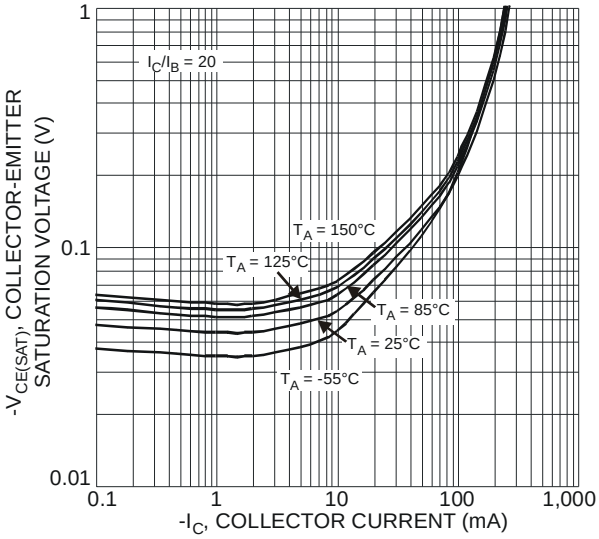


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

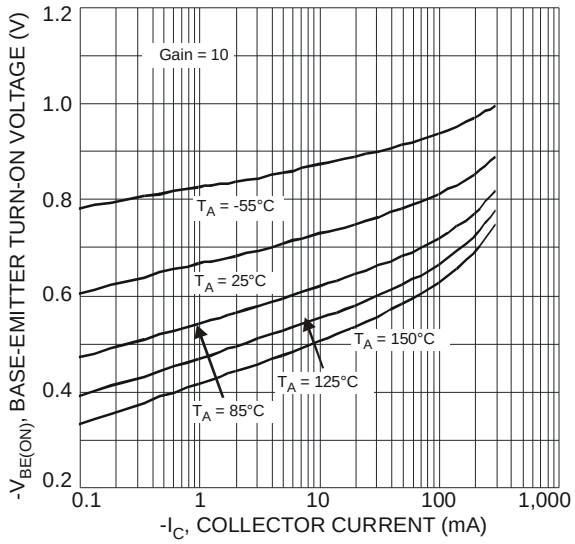


Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

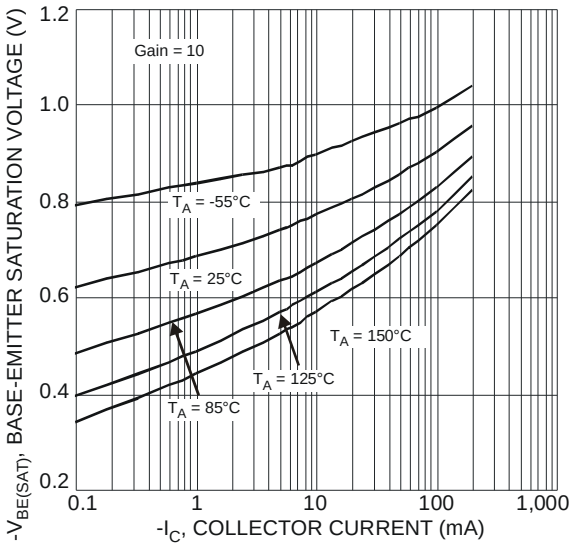
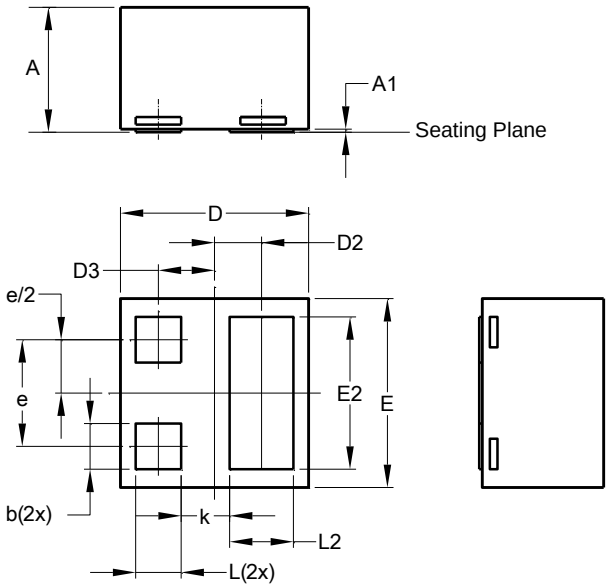


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions

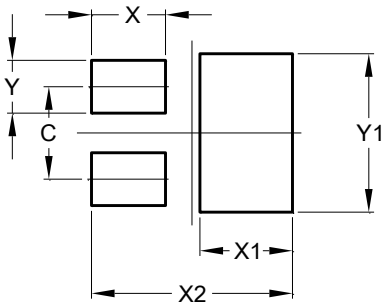
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN0606-3			
Dim	**Min**	**Max**	**Typ**
A	0.36	0.42	0.39
A1	0	0.05	0.02
b	0.10	0.20	0.15
D	0.57	0.67	0.62
D2	0.155 BSC		
D3	0.185 BSC		
E	0.57	0.67	0.62
E2	0.40	0.60	0.50
e	0.35 BSC		
k	0.16 REF		
L	0.09	0.21	0.15
L2	0.11	0.31	0.21
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.350
X	0.280
X1	0.350
X2	0.760
Y	0.200
Y1	0.600

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